



제25회 한국반도체학술대회

The 25th Korean Conference on Semiconductors

2018년 2월 5일(월)-7일(수), 강원도 하이원리조트 컨벤션 호텔

2018년 2월 7일(수), 16:15-17:30

Room I (청옥II+III, 6층)

K. Memory (Design & Process Technology) 분과

[WI4-K] Phase-Change Memory

좌장: 권용우 교수(홍익대학교), 노광명 수석(SK 하이닉스)

WI4-K-1 16:15-16:45	[초청] New Memory in the New Data Centric Economy 유경창, 류혜영, 임선영, 린홍준, 김인동, 한진만 <i>삼성전자</i>
WI4-K-2 16:45-17:00	Understanding of Reactive Ion Etching (RIE) Induced Damage Mechanism and Development in Sub-20nm PRAM Patterning Hyejin Choi, Bok-yeon Won, JaehunSeo, Jung-Ik Oh, Yoochul Gong, Olk-Kwon, Jongchul Park, Kyungsub Shin, and Ho-kyu Kang <i>Process development Team, Semiconductor R&D Center Samsung Electrics Co., Ltd</i>
WI4-K-3 17:00-17:15	Analysis of Threshold Switching Characteristics of Te Based Selector Tae Yoon Kim ¹ , Gwang Ho Baek ² , Gabriel Jang ¹ , Da Seul Hyun ¹ , and Jin Pyo Hong ^{1,2} <i>¹Novel Functional Materials and Devices Lab, The Research Institute for Natural Science, Department of Physics, Hanyang University, ²Division of Nano-Scale Semiconductor Engineering, Hanyang University</i>
WI4-K-4 17:15-17:30	Flexible 1 Schottky Diode-1 Phase Change Memory on Plastics via Physical Exfoliation Do Hyun Kim ¹ , Han Eol Lee ¹ , Byoung Kuk You ¹ , Il-Suk Kang ² , and Keon Jae Lee ¹ <i>¹Department of Materials Science and Engineering, KAIST, ²Nano Research Division, National NanoFab Center</i>